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U.S. UTILITY Patent Application

PATENT NUMBER and  
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10008204	12/05/2001	438		2812	

\*\*APPLICANTS: Chern Geeng-Chuan; Levi Amitay; Lee Dana;

\*\*CONTINUING DATA VERIFIED:

\*\* FOREIGN APPLICATIONS VERIFIED:

PG-PUB ☐ DO NOT PUBLISH ☐

RESCIND ☐

Foreign priority claimed ☐ yes ☐ no

35 USC 119 conditions met: ☐ yes ☐ no

Verified and Acknowledged Examiners's initials

ATTORNEY DOCKET NO

2102397-991220

TITLE : Method of forming different oxide thickness for high voltage transistor and memory cell tunnel dielectric

U.S. DEPT. OF COMM./PAT. & TM.-PTO-438L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		Primary Examiner	DRAWING	
Amount Due	Date Paid		Sheets Drwg.	Figs. Drwg.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner	
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